

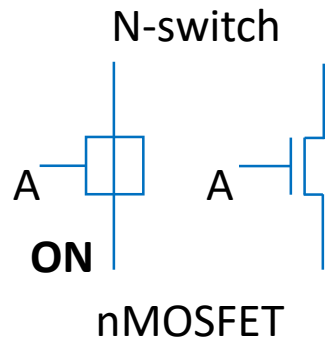
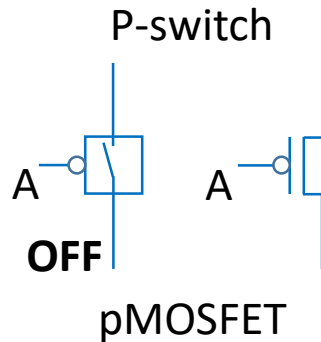
Lecture 16

Introduction to Integrated Circuit Design

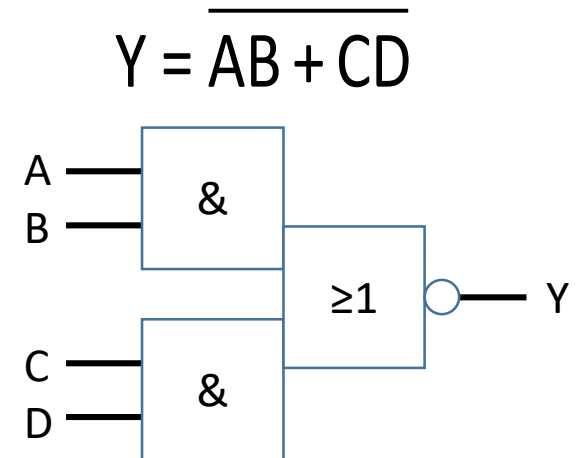
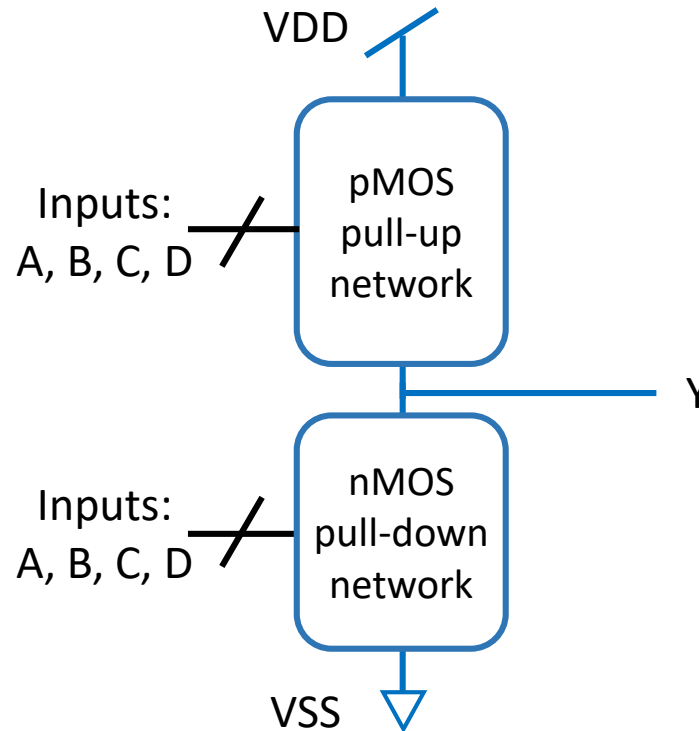
Course summary

Designing gates with switches

Already the first lecture we learnt how to design gates with switches
and in CMOS there are two complementary switches

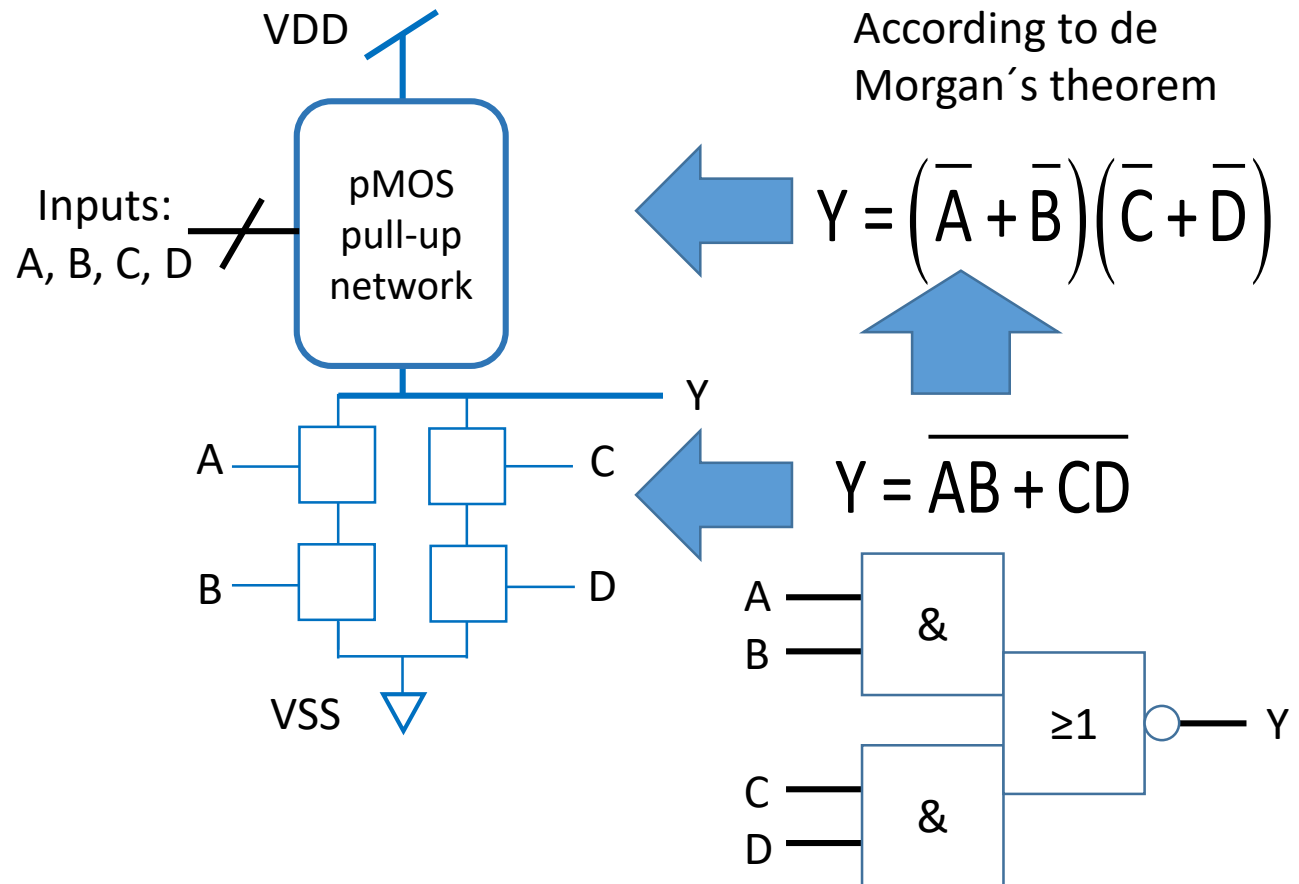
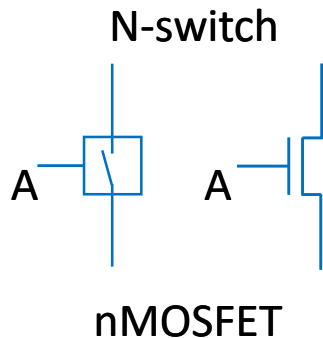
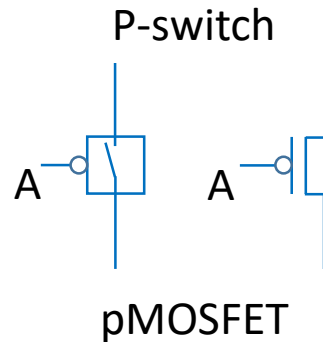


input A is HIGH



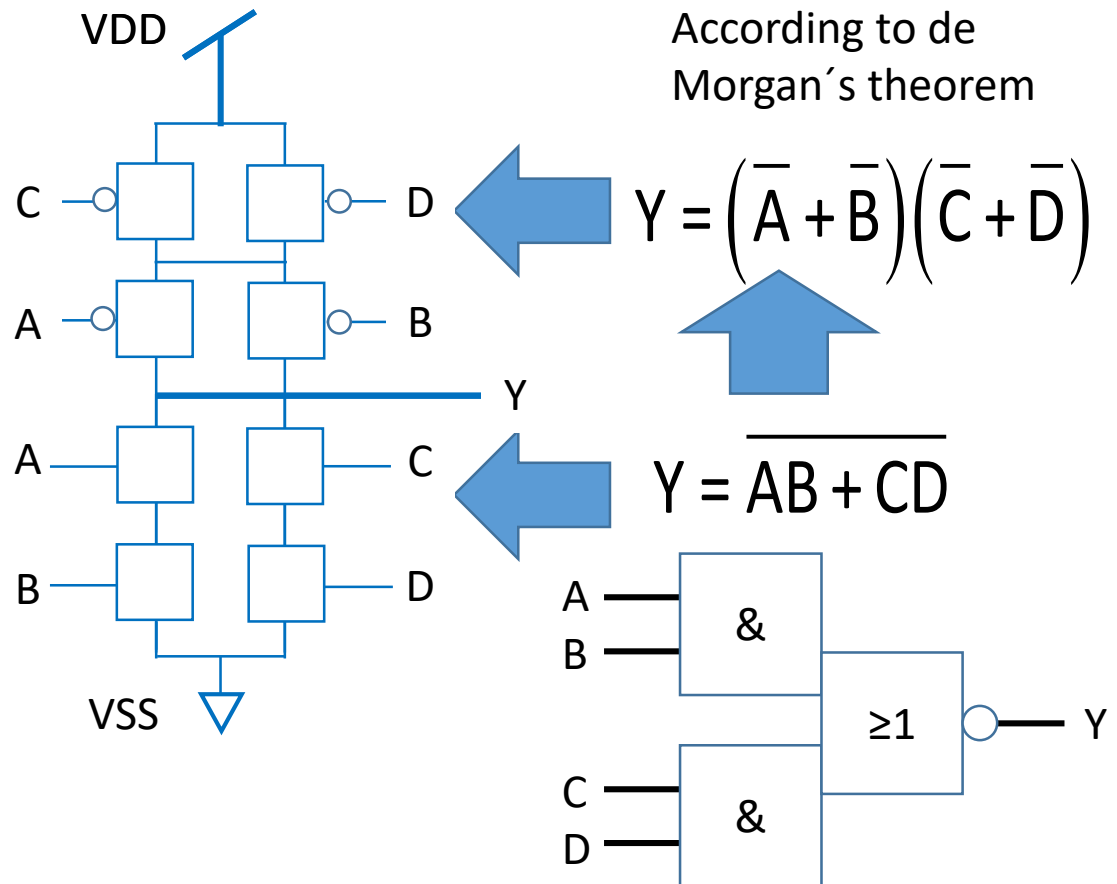
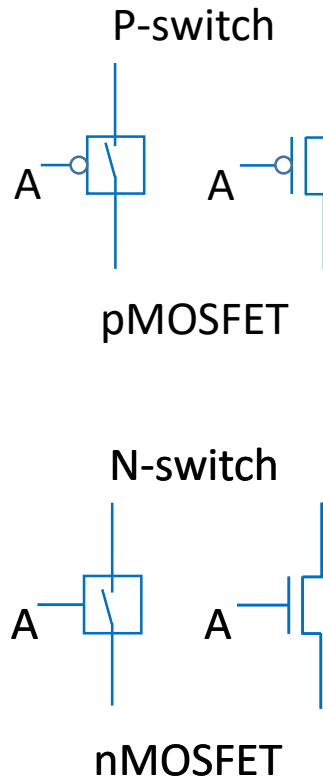
Designing gates with switches

Already the first lecture we learnt how to design gates with switches and in CMOS there are two complementary switches



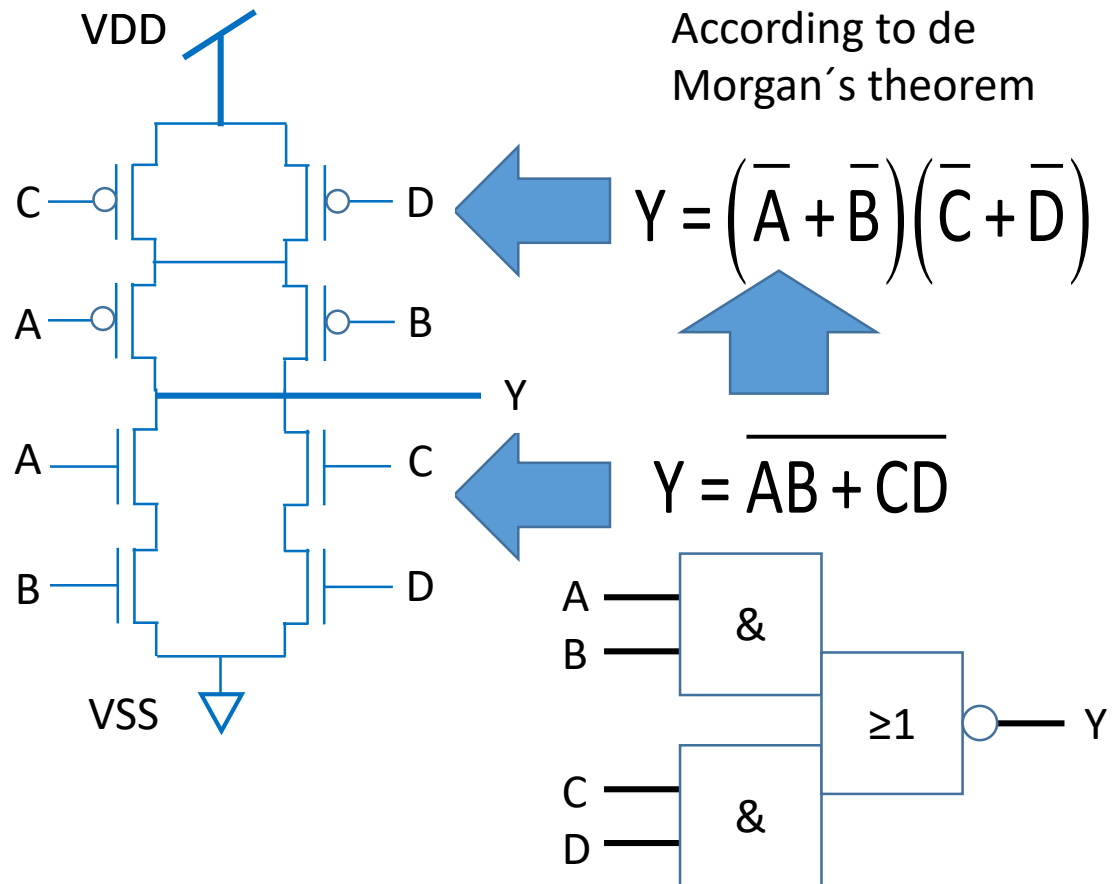
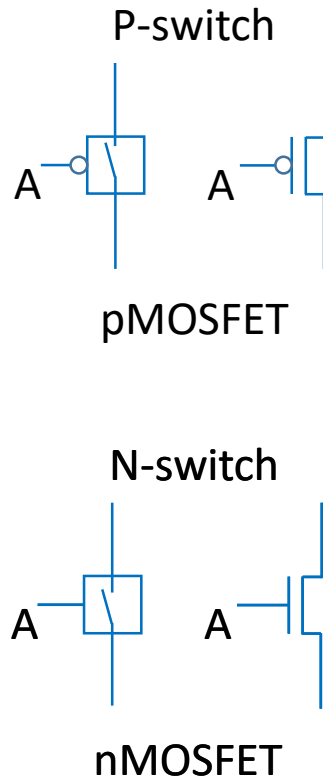
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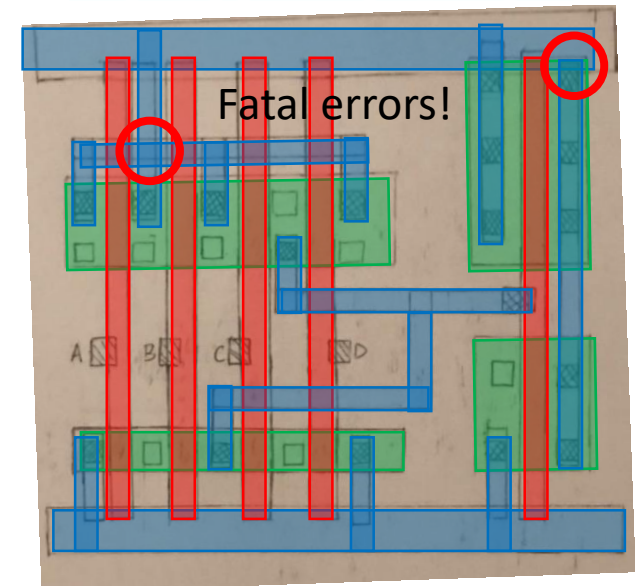
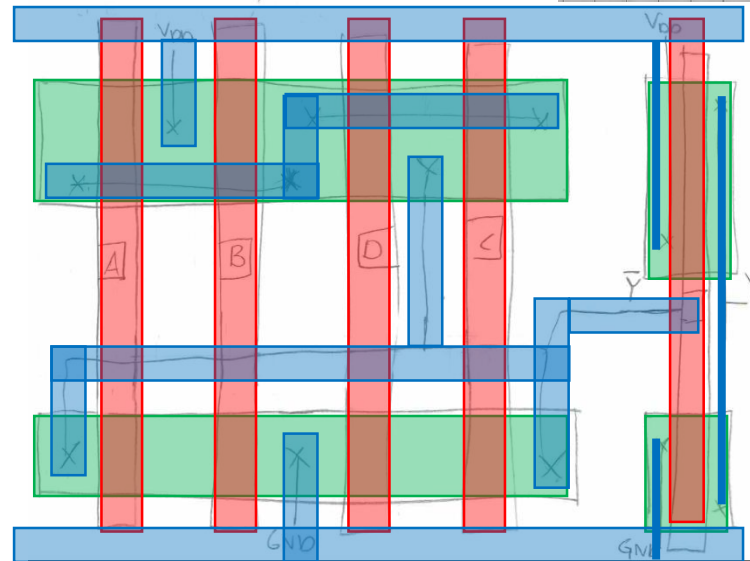
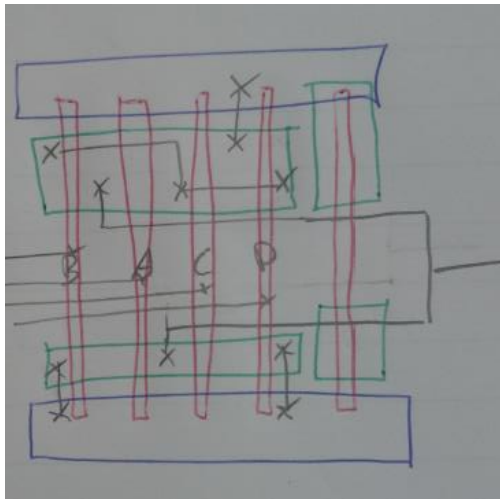
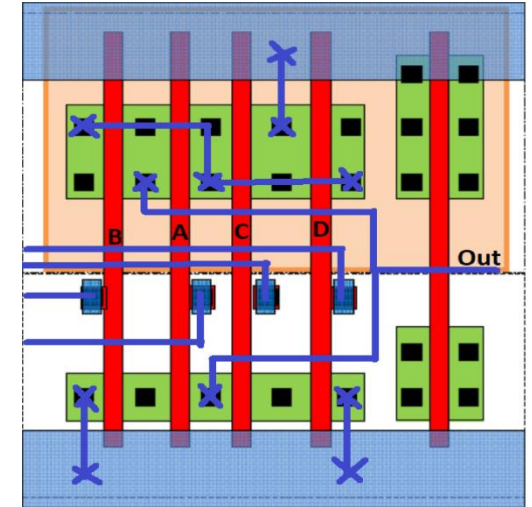
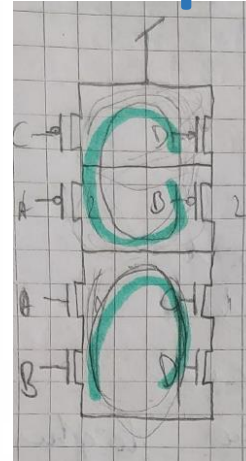
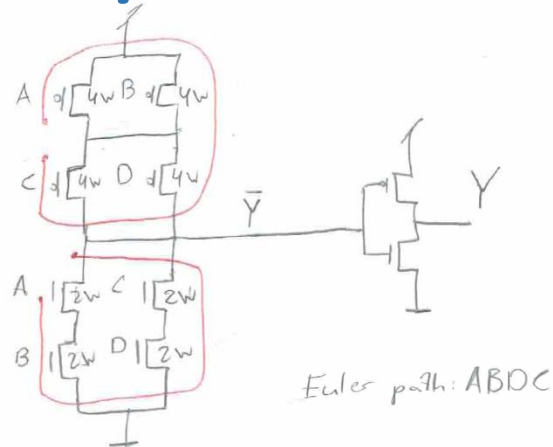
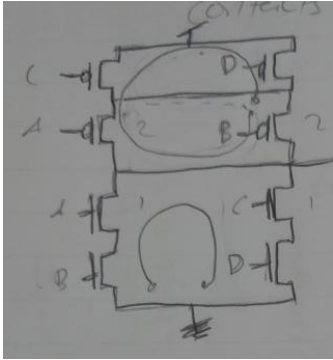


Designing gates with switches

Already the first lecture we learnt how to design gates with switches
and in CMOS there are two complementary switches



Layout and Euler paths

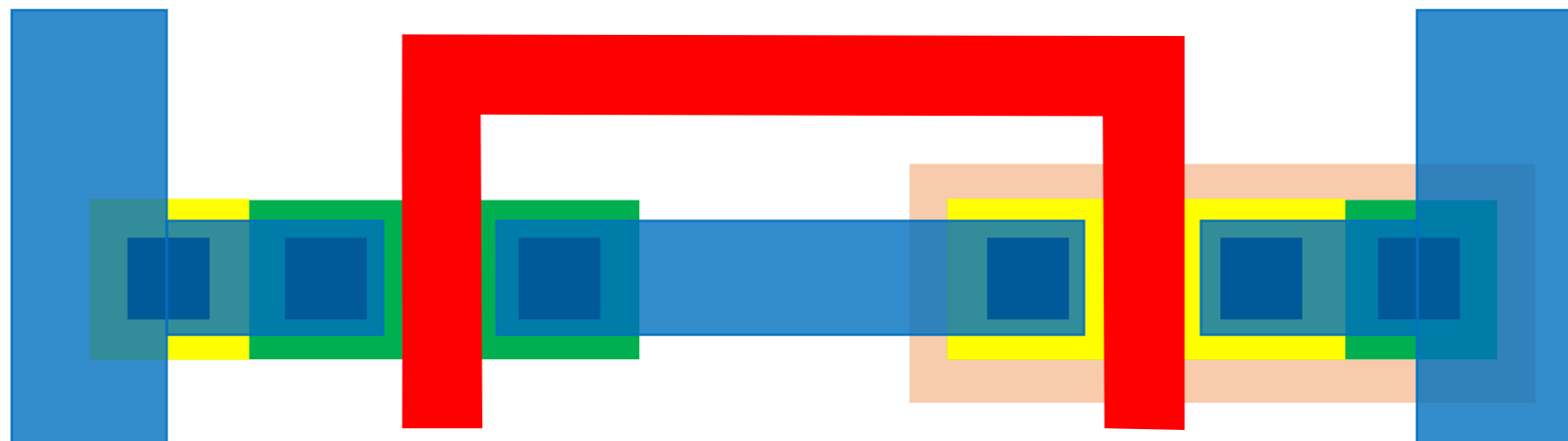
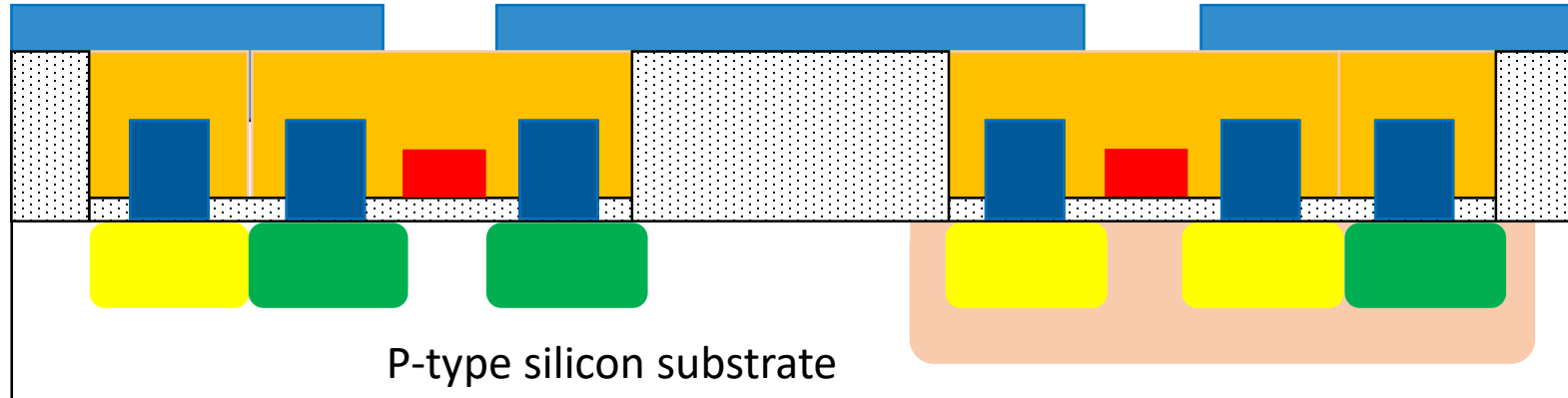


Fabrication

- Chips are built in huge factories called fabs
- Contain clean rooms as large as football fields



Inverter mask set and fabrication



Yellow P+ select

Black Contact cuts

Blue Metal wires

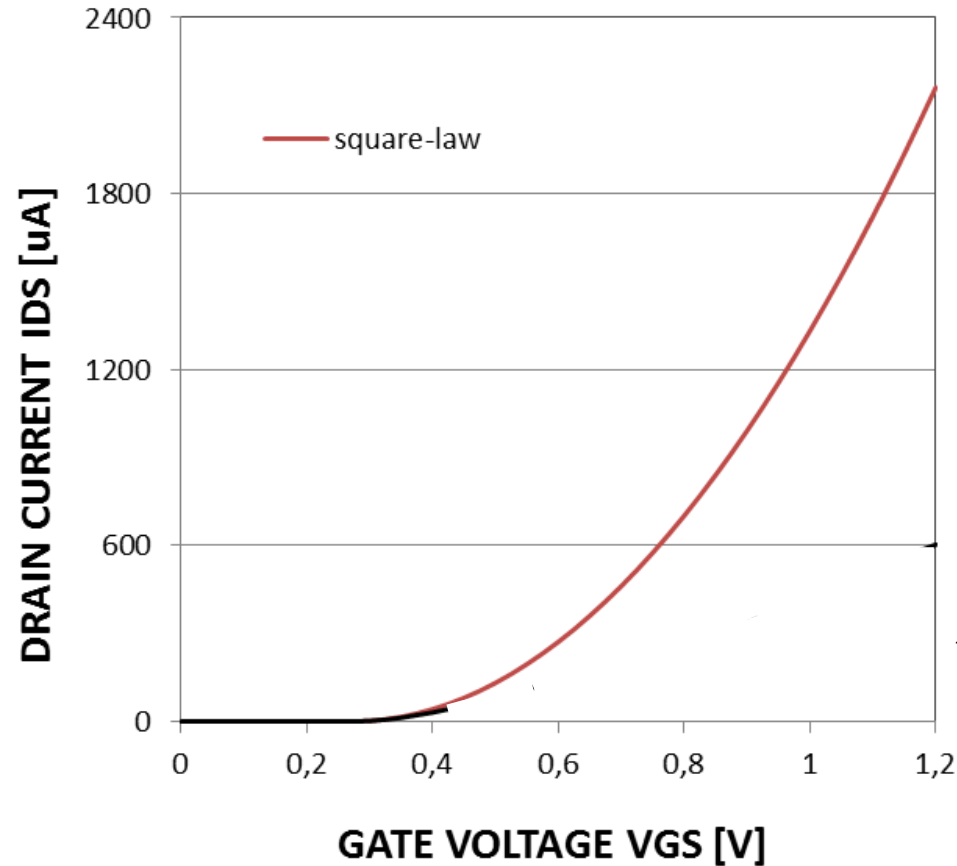
Red Poly gate

Green Active areas

Light orange N-well

MOSFET – a square-law device

MOSFET transfer characteristic



$$I_{DSAT} = \frac{k}{2}(V_{GS} - V_T)^2$$

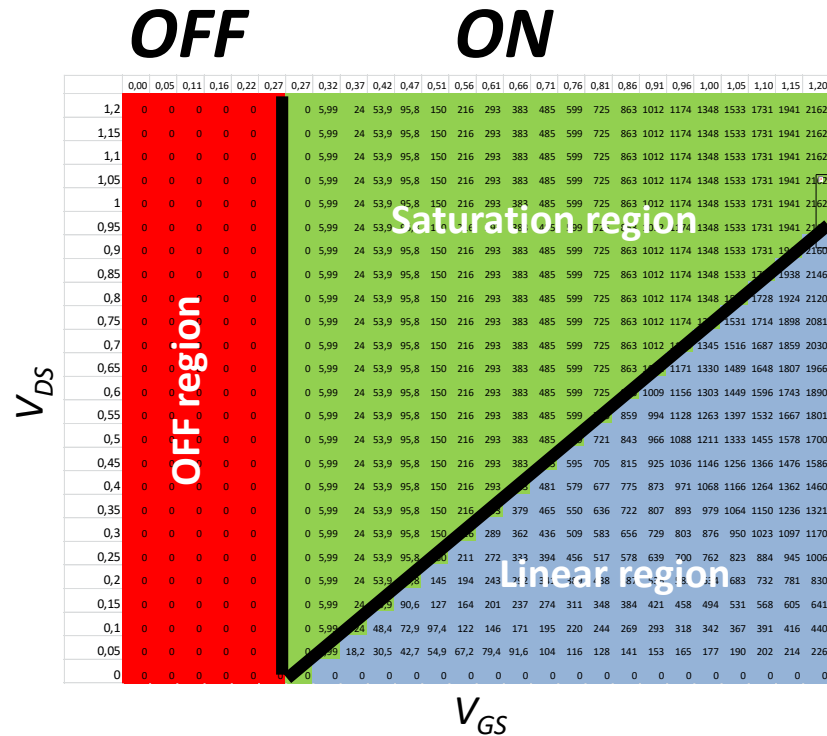
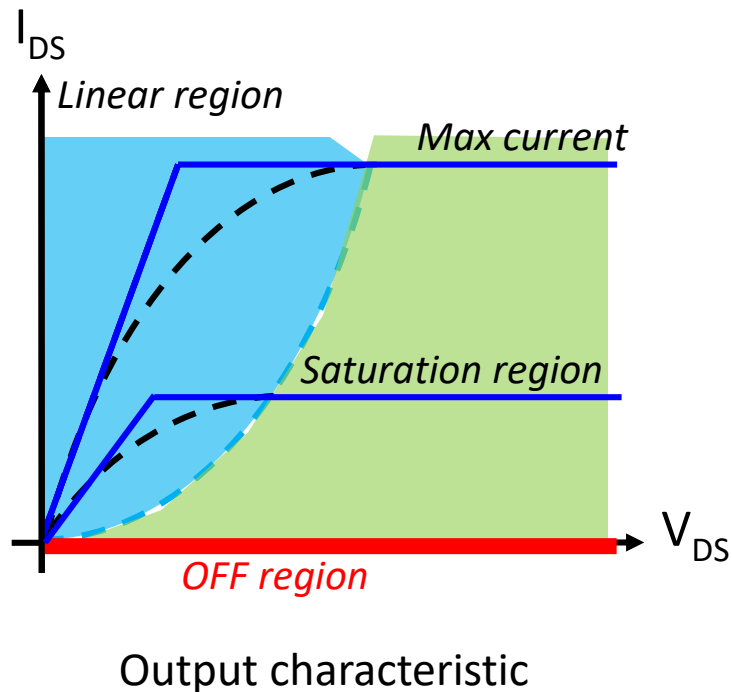
$$V_{DSAT} = V_{GS} - V_T$$

$$I_{DSAT} = \frac{k}{2}(V_{GS} - V_T)V_{DSAT}$$

$$V_{DSAT} < V_{GS} - V_T$$

MOSFET models

Models can predict I_{DS} for any V_{GS}/V_{DS}



CMOS Inverter

Equal saturation currents
yields the switching voltage

$$I_{dsp} = \frac{k_P}{2} (V_{DD} - V_{IN} + V_{TP})^2$$

$$I_{dsn} = \frac{k_N}{2} (V_{IN} - V_{TN})^2$$

$$V_{sw} = V_{TN} + \frac{\Delta V}{1 + \sqrt{x}}, \quad x = \frac{k_N}{k_P}$$

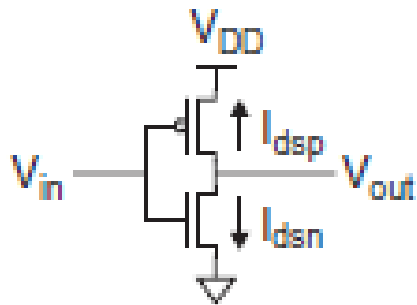
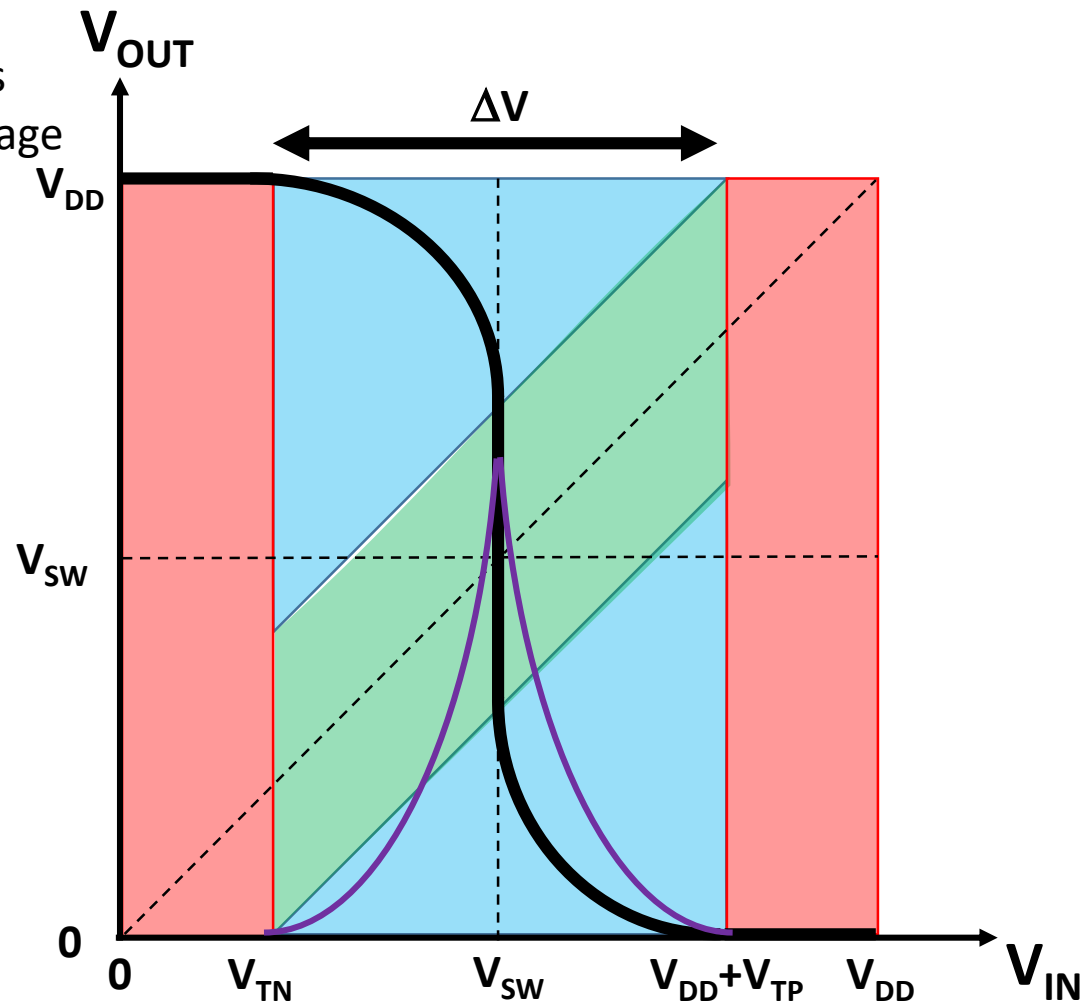


FIGURE 2.25
A CMOS inverter



CMOS Inverter

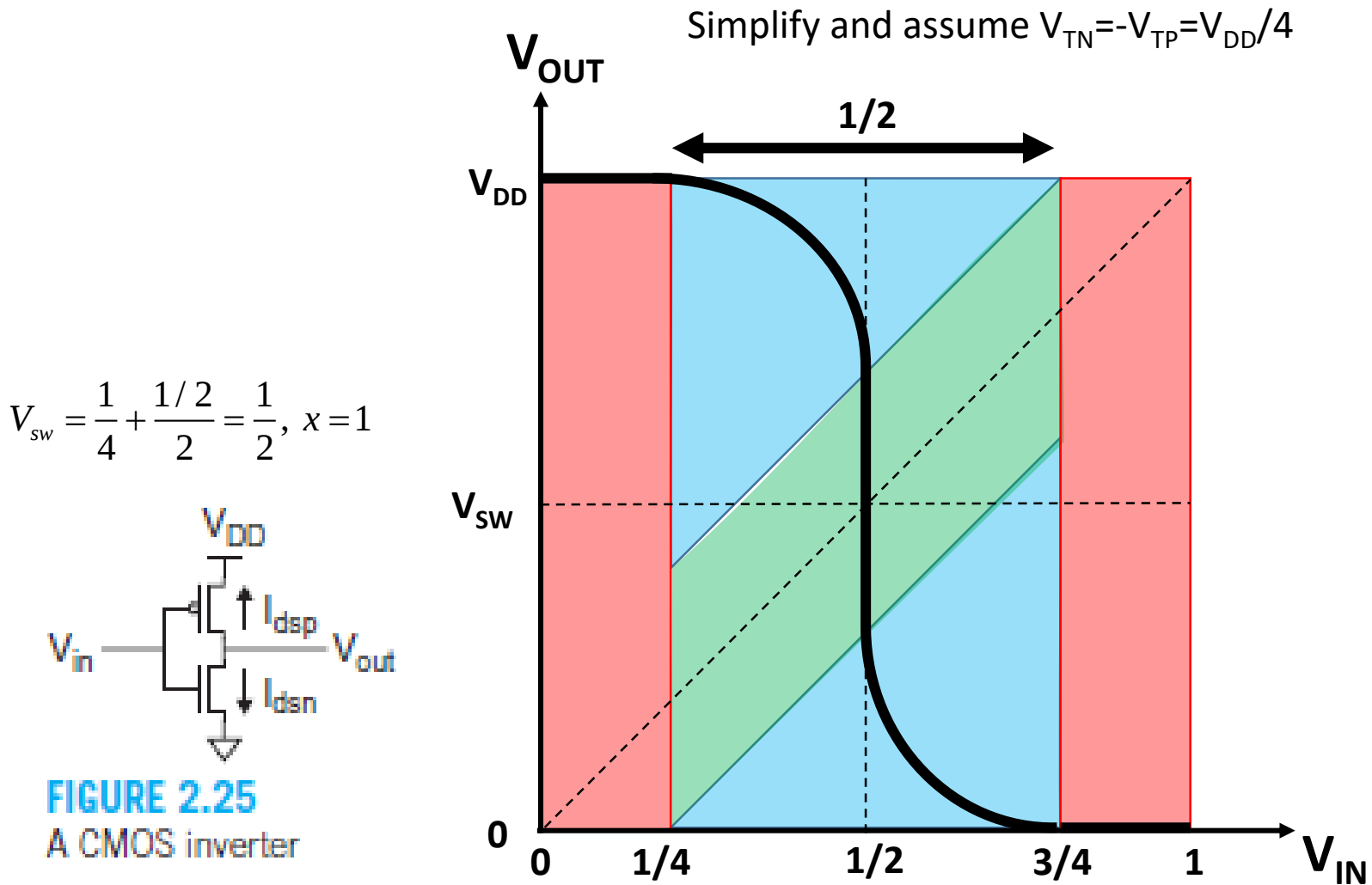
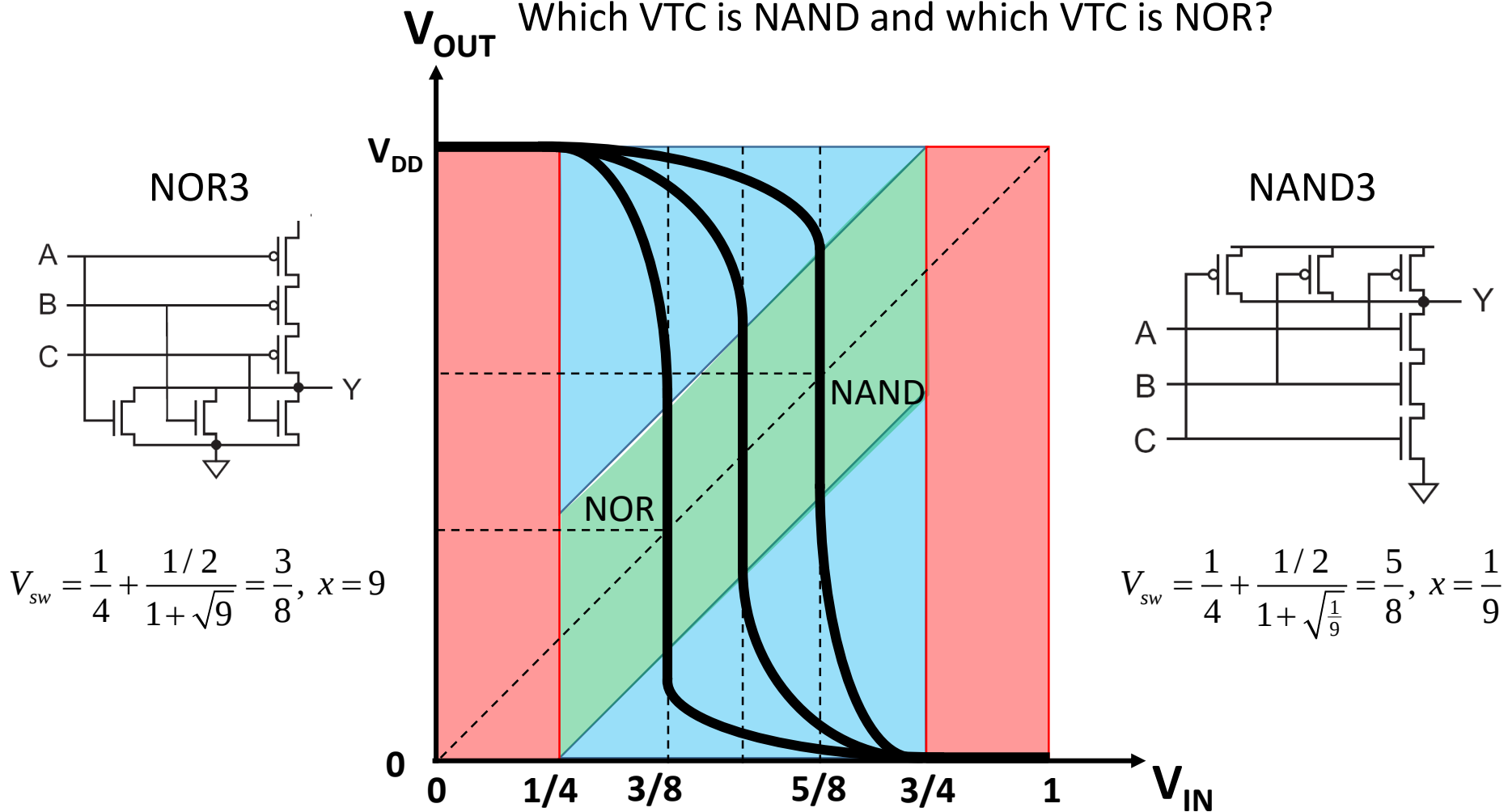


FIGURE 2.25
A CMOS inverter

NAND/NOR VTC

Which VTC is NAND and which VTC is NOR?



CMOS Inverter – Noise margins

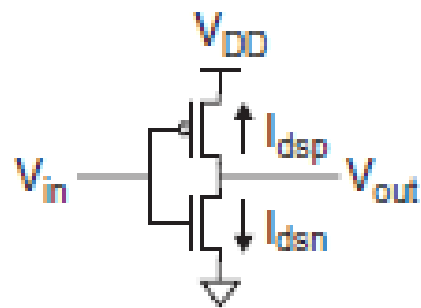
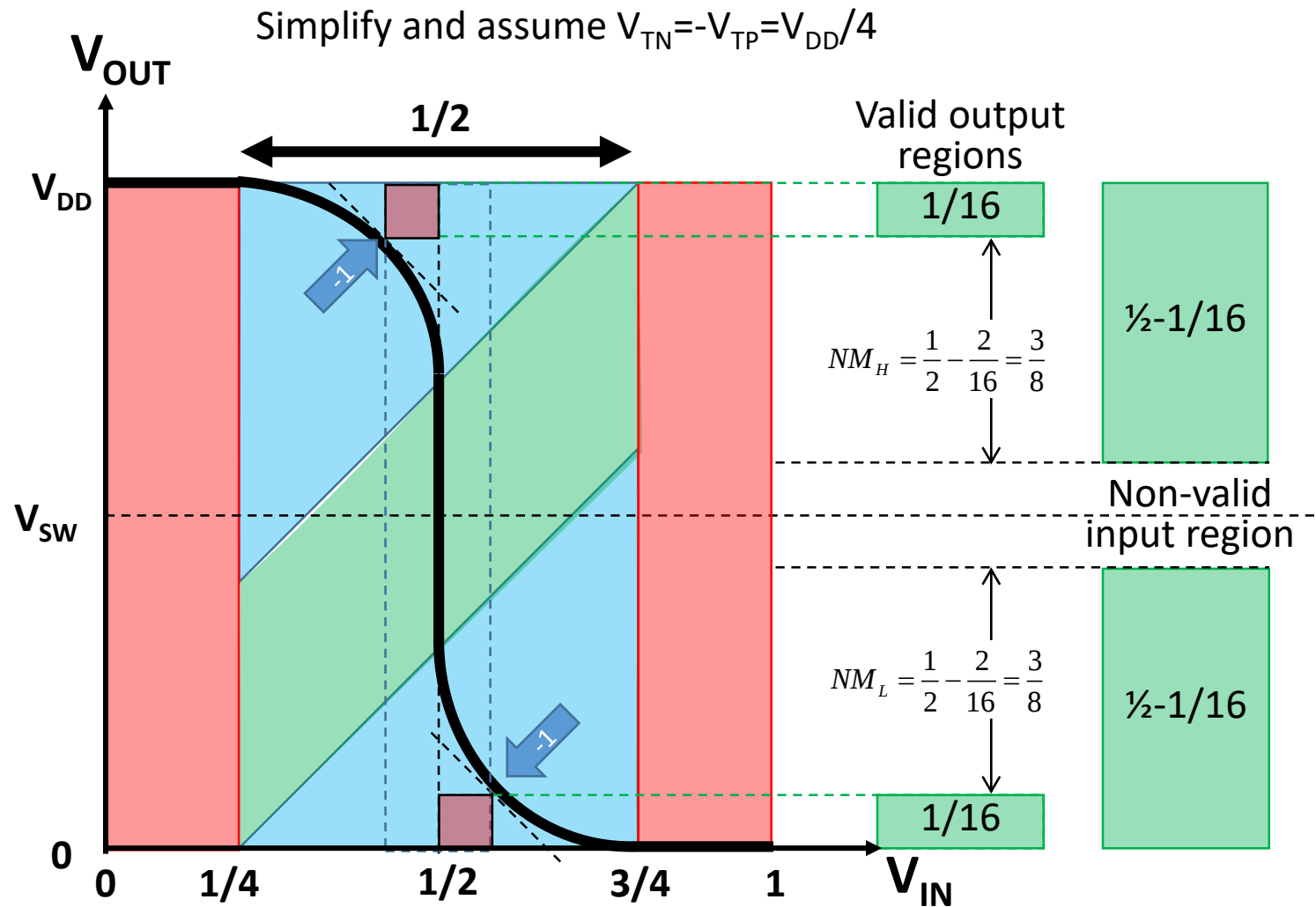
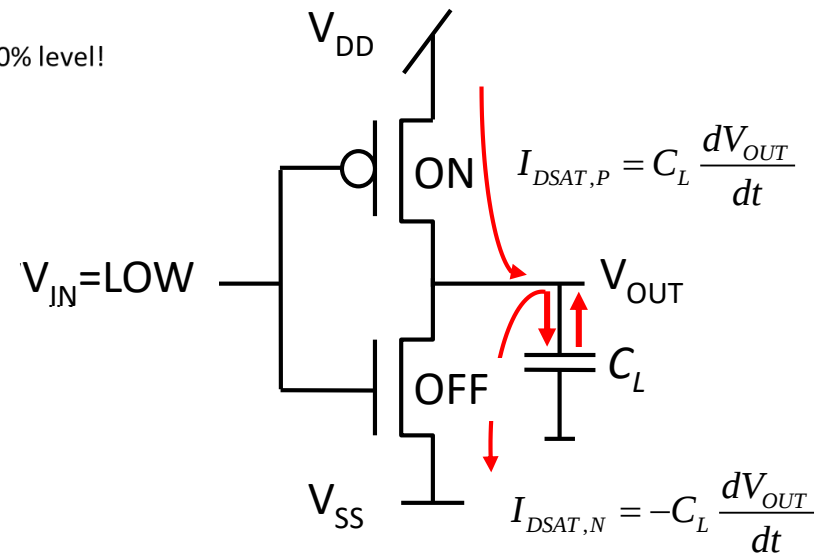
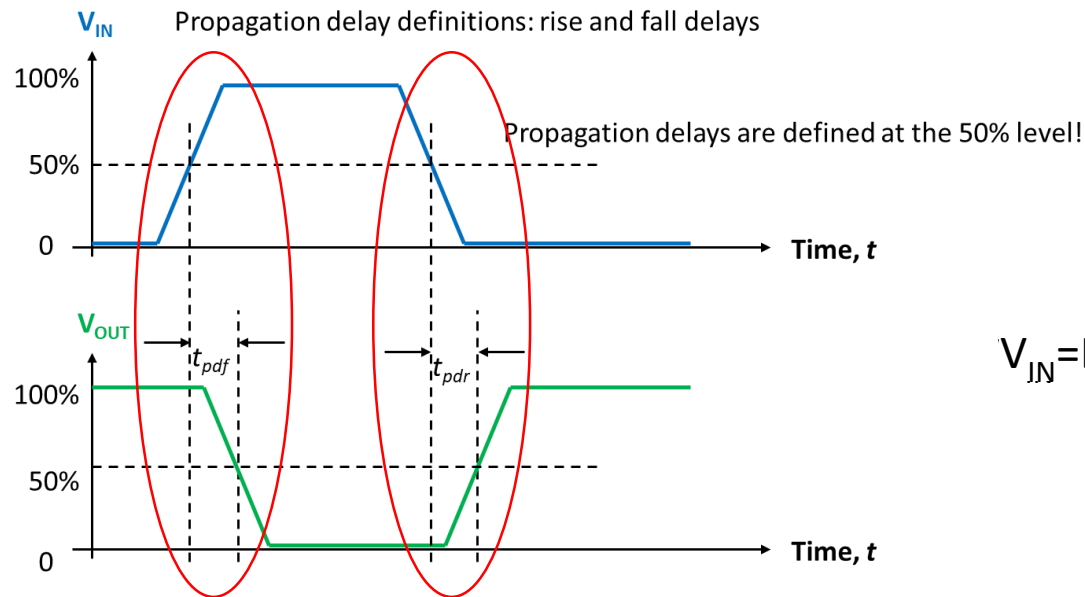


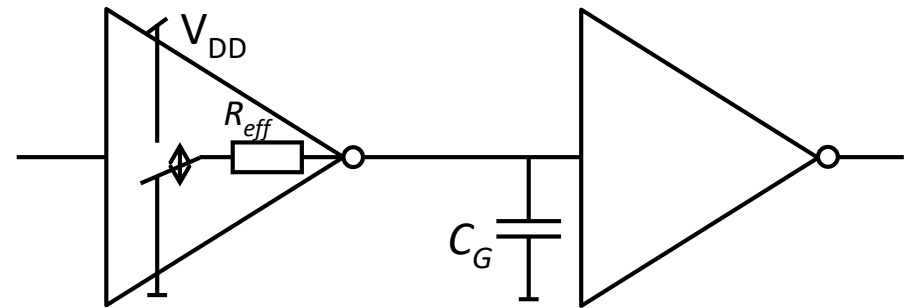
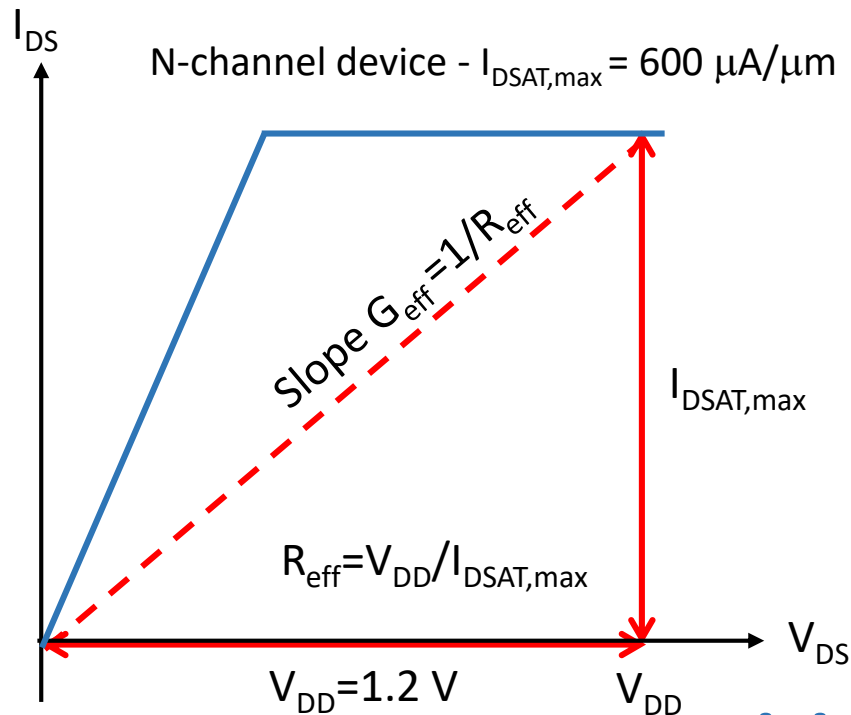
FIGURE 2.25
A CMOS inverter



Switching the inverter



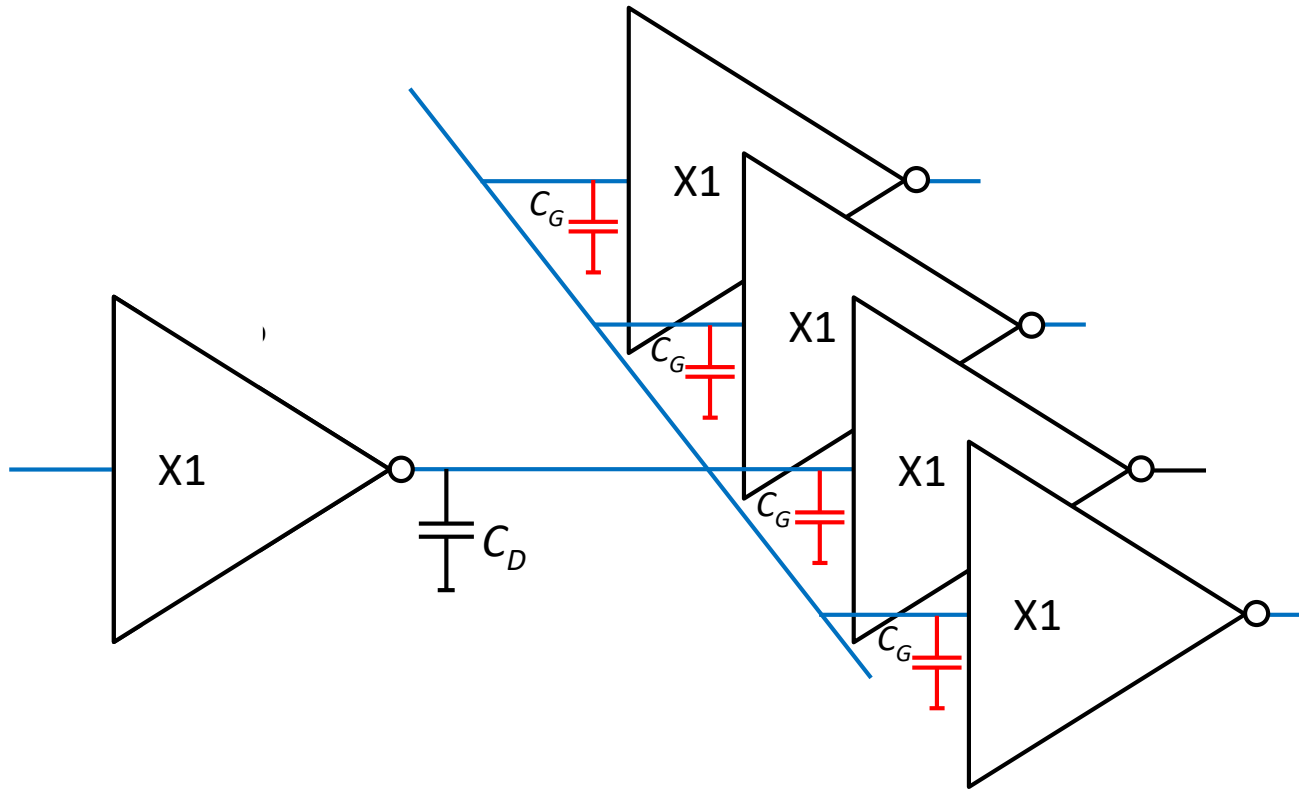
Defining the effective resistance . . .



Defining the ideal, non-parasitic delay
 $\tau = 0.7R_{eff}C_G = 5\text{ ps}$ in 65 nm CMOS

. . . and reference delay
 τ

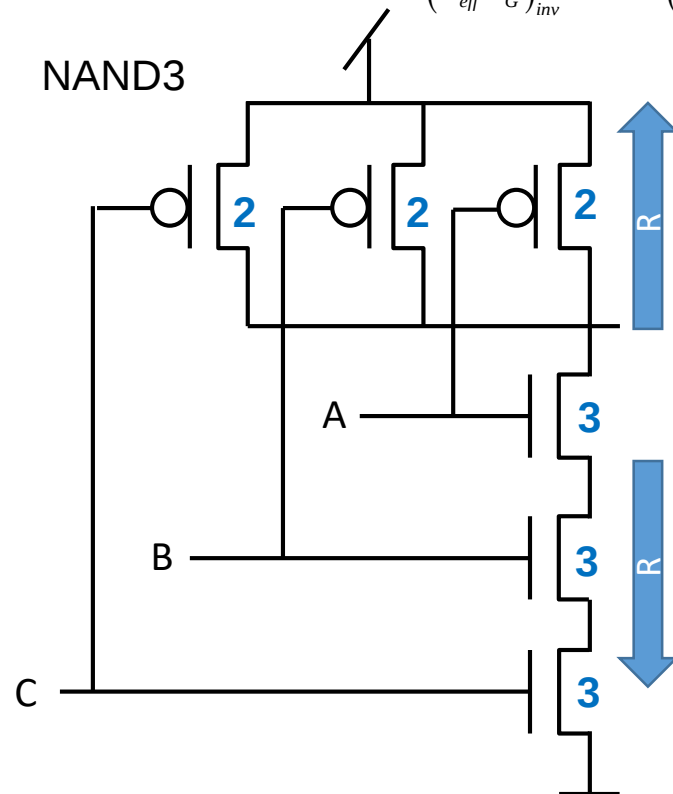
FO4 delay



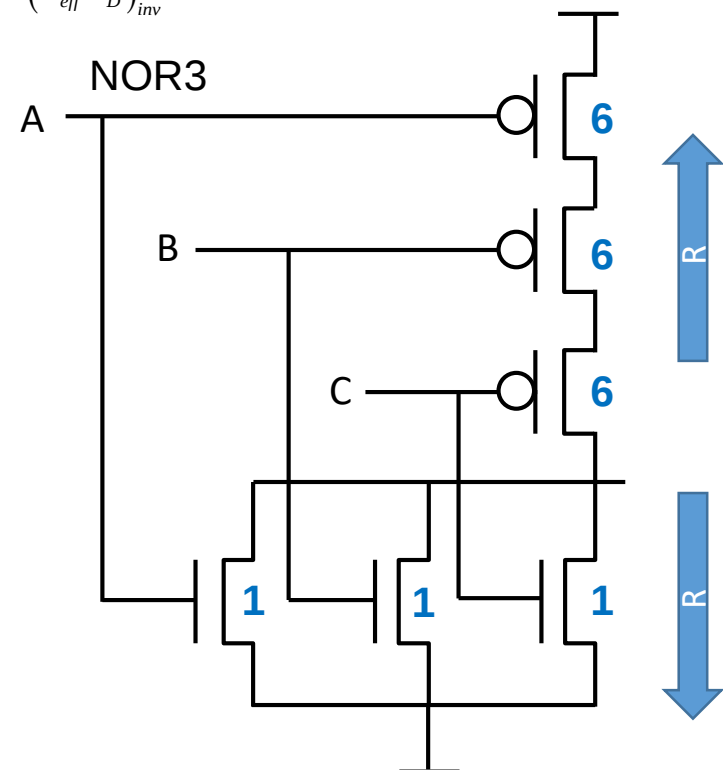
The FO4 propagation delay becomes $t_{pd} = 0.7R_{eff}(C_D + 4C_G) = \underbrace{0.7R_{eff}C_G}_{\tau} (p_{inv} + 4) = 5 \text{ ps} \times 5 = 25 \text{ ps}$

Defining logical effort

$$g = \frac{(R_{eff} C_{IN})_{gate}}{(R_{eff} C_G)_{inv}} \quad p = \frac{(R_{eff} C_D)_{gate}}{(R_{eff} C_G)_{inv}} = p_{inv} \frac{(R_{eff} C_D)_{gate}}{(R_{eff} C_D)_{inv}}$$

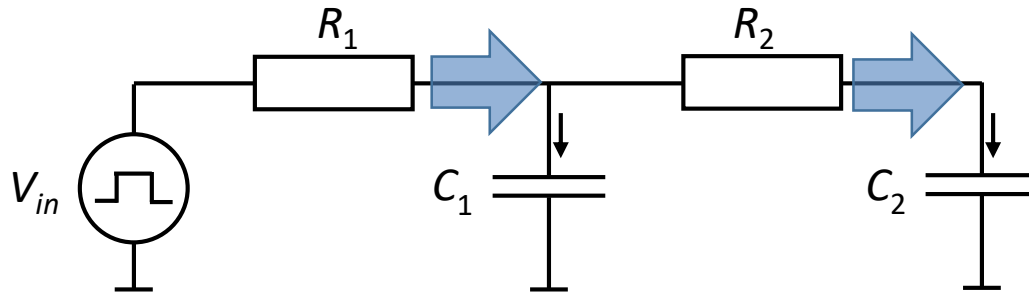


$$g = \frac{R_{eff} 5C}{R_{eff} 3C} = \frac{5}{3} \quad p = \frac{R_{eff} 9C_D}{R_{eff} 3C} = 3p_{inv}$$



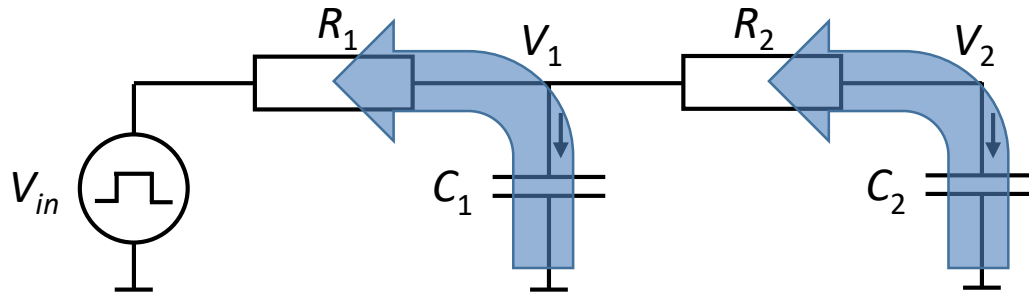
$$g = \frac{R_{eff} 7C}{R_{eff} 3C} = \frac{7}{3} \quad p = \frac{R_{eff} 9C_D}{R_{eff} 3C} = 3p_{inv}$$

Wire delay



Each resistance is multiplied by its downstream capacitance!

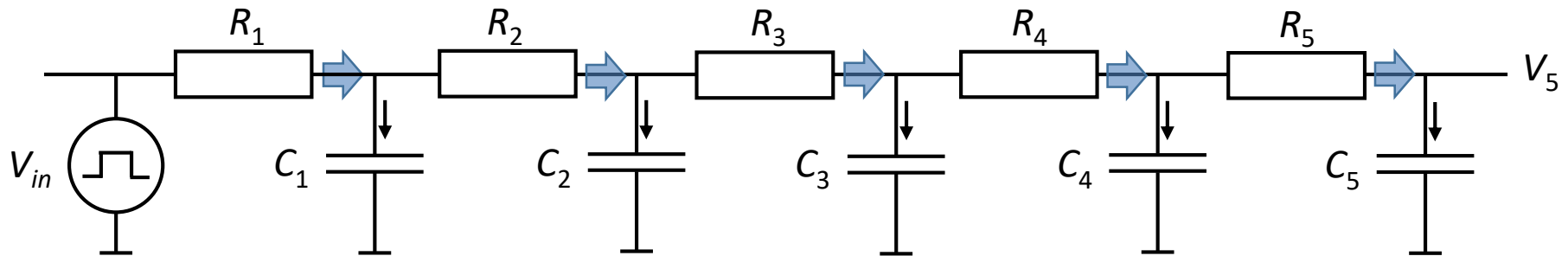
$$T_E = R_1(C_1 + C_2) + R_2C_2$$



Or: Each capacitance is multiplied by its upstream capacitance!

$$T_E = R_1C_1 + (R_1 + R_2)C_2$$

Elmore delay model



Estimate the propagation delay through the RC ladder knowing that the output voltage is given by

$$V_5 = V_{50} + V_{51}e^{-t/\tau_1} + V_{52}e^{-t/\tau_2} + V_{53}e^{-t/\tau_3} + V_{54}e^{-t/\tau_4} + V_{55}e^{-t/\tau_5}$$

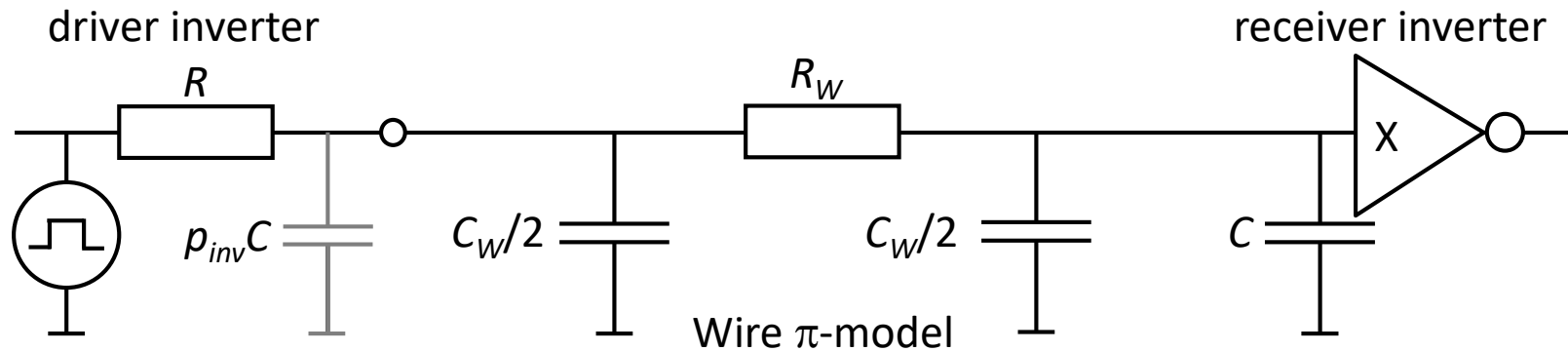
and realizing that we cannot determine any of the parameters involved analytically!

Hence, we use the Elmore delay model based on the assumption that one of the five time constants is dominant!

If so, the dominant time constant T_E (after W. C. Elmore) can be obtained by multiplying each of the resistances with its downstream capacitance!

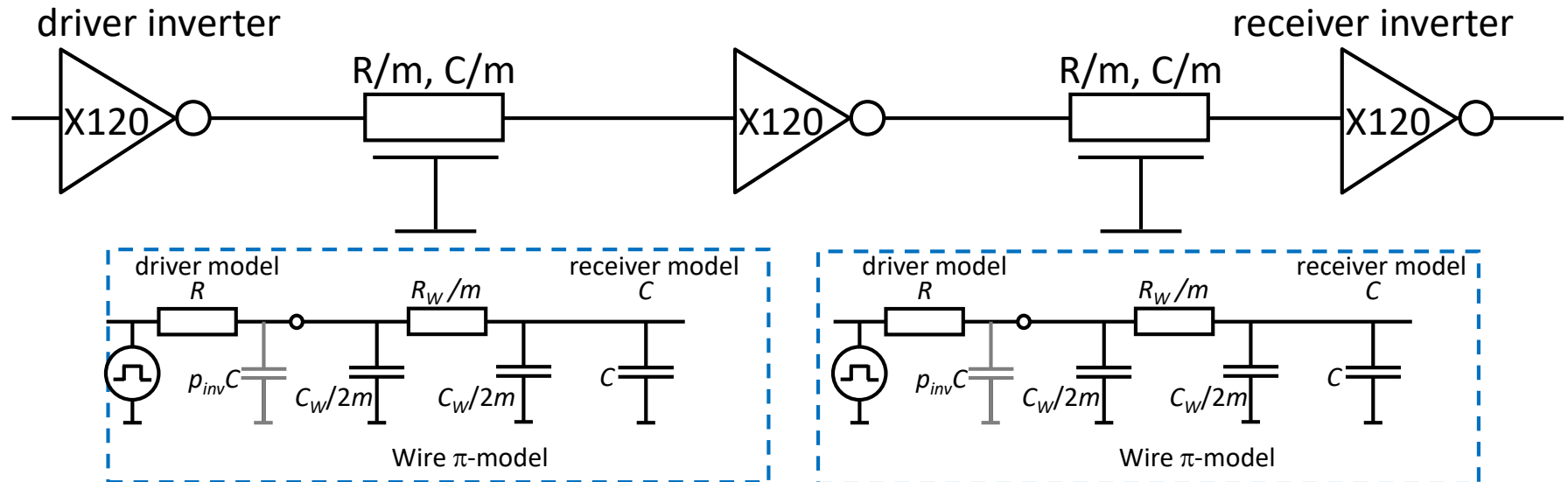
$$T_E = R_1(C_1 + C_2 + C_3 + C_4 + C_5) + R_2(C_2 + C_3 + C_4 + C_5) + R_3(C_3 + C_4 + C_5) + R_4(C_4 + C_5) + R_5C_5$$

Sizing the driver



1. Start by defining wire effort $W_E = \frac{R_W C_W}{R C_{inv}}$
2. Elmore $T_E = RC(p_{inv} + 1) + RC_W + R_W C + \frac{R_W C_W}{2}$
3. Normalize $d = p_{inv} + 1 + W_E \frac{R}{R_W} + \frac{R_W}{R} + \frac{W_E}{2}$
4. Find minimum $\frac{\partial d}{\partial R} = \frac{W_E}{R_W} - \frac{R_W}{R^2} = 0 \rightarrow R = \frac{R_W}{\sqrt{W_E}}$

Repeater insertion

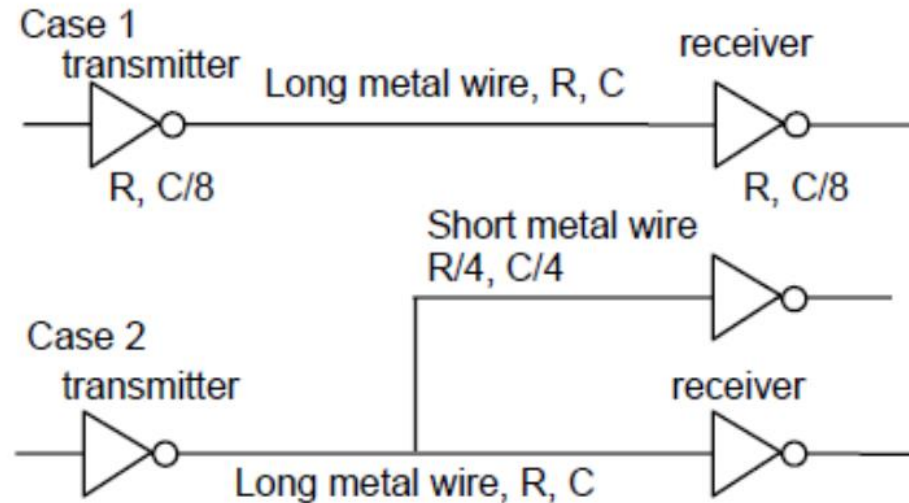


Normalized delay m segments
$$d = m \left(1 + p_{inv} + \frac{W_E}{m^2} \frac{mR}{R_W} + \frac{R_W}{mR} + \frac{W_E}{2m^2} \right)$$

Find minimum, i.e. $\partial d / \partial m = 0$, i.e. for $m = \frac{1}{2} \sqrt{W_E}$

Minimum normalized delay is $d = 4\sqrt{W_E}$.

Divide and conquer

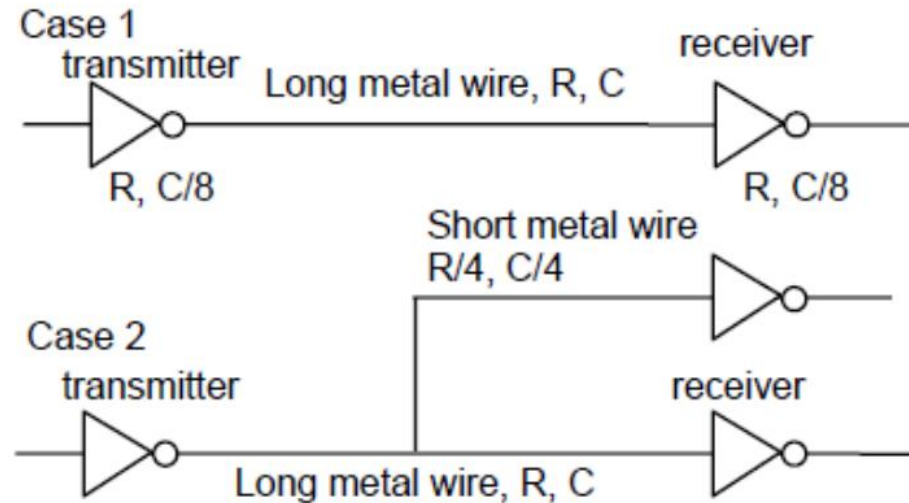


If they ask for the difference between $x+a$ and $x+b$, i.e. $a-b$, we do not need to calculate x !
 Branch contribution to delay is branch capacitance times upstream resistance

$$T_{E,branch} = \left(\frac{C}{4} + \frac{C}{8} \right) \left(R + \frac{R}{2} \right) = \frac{9}{16} RC$$

Total Elmore time constant is then $39RC/16 \approx 2.5RC$

Divide and conquer



The wire to the other receiver is shorter, only $\frac{3}{4}$ of the other wire length

Hence, the main path to the other receiver has resistance $\frac{3R}{4}$ and capacitance $\frac{3C}{4}$

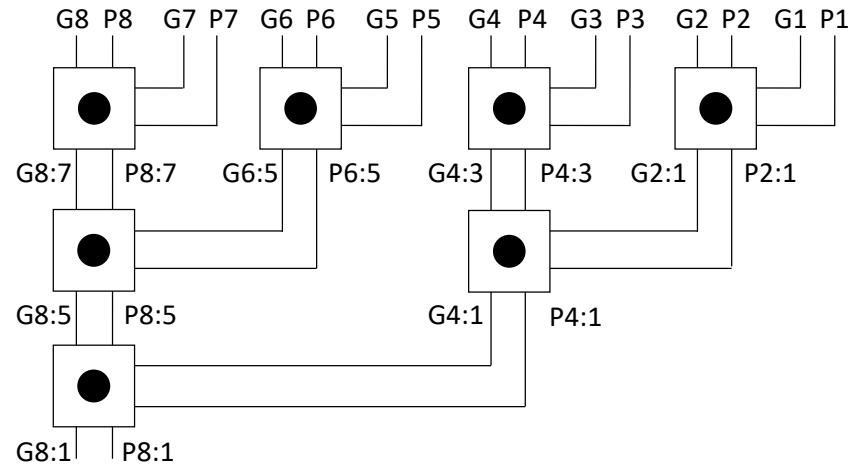
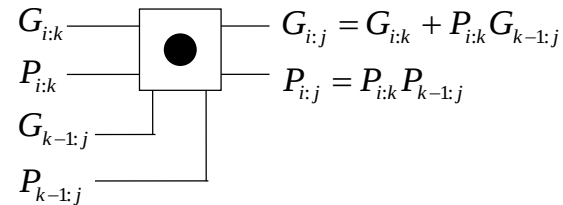
Main path delay contribution is found to be $\frac{22RC}{16}$, and branch contribution is $\frac{15RC}{16}$

$$T_{E,branch} = \left(\frac{C}{2} + \frac{C}{8} \right) \left(R + \frac{R}{2} \right) = \frac{15}{16} RC$$

Total Elmore time constant is then $\frac{37RC}{16} \approx 2.3RC$

The dot operator

The “dot operator” is associative and idempotent



Show that $(G_{4:3}, P_{4:3}) \bullet (G_{2:1}, P_{2:1}) = G_4 + P_4 (G_3 + P_3 (G_2 + P_2 G_1)), P_4 P_3 P_2 P_1$

Show that $(G_{4:2}, P_{4:2}) \bullet (G_{3:1}, P_{3:1}) = G_4 + P_4 (G_3 + P_3 (G_2 + P_2 G_1)), P_4 P_3 P_2 P_1$

The dot operator

- Properties of the dot operator

- Associativity i.e. parallelization

- Easy to prove since logical OR and AND operations are associative

- With the definition $G_{i:i-1}, P_{i:i-1} = (G_i, P_i) \bullet (G_{i-1}, P_{i-1})$ G_i becomes the carry-out signal at stage i of an adder

- The operation is idempotent

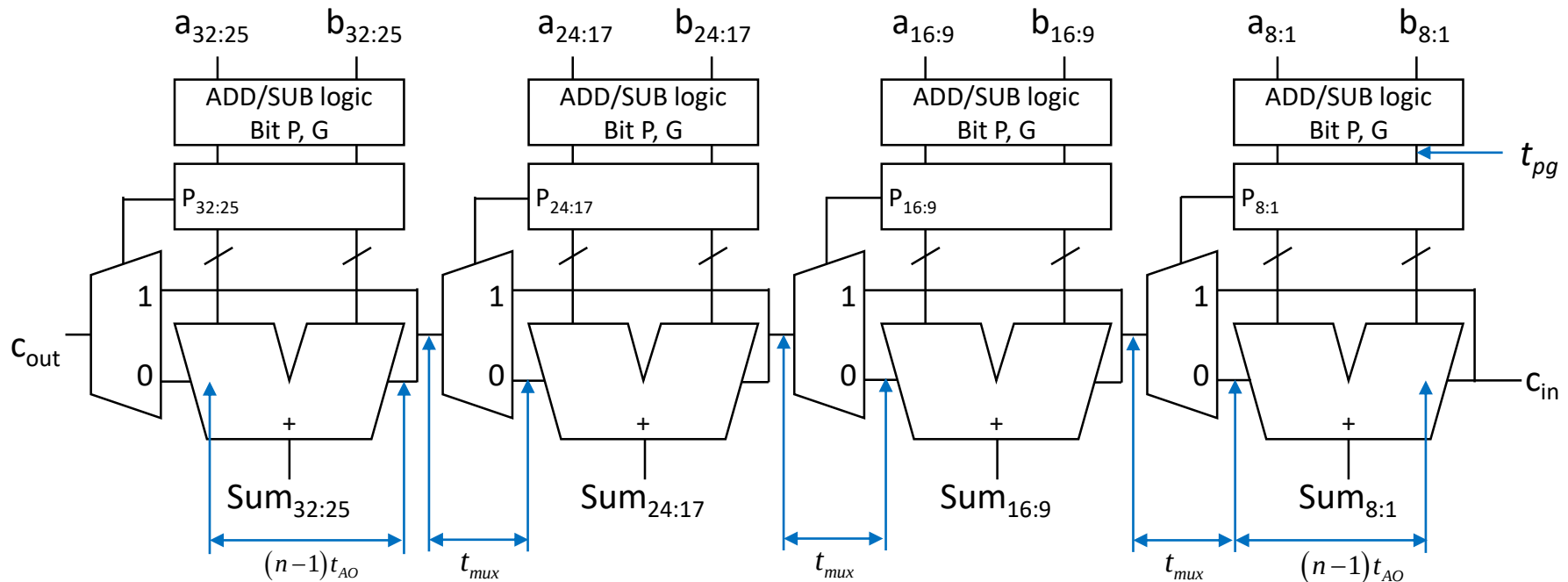
$$(G_{i:i-1}, P_{i:i-1}) \bullet (G_{i:i-1}, P_{i:i-1}) = (G_{i:i-1} + P_{i:i-1}G_{i:i-1}, P_{i:i-1}P_{i:i-1}) = (G_{i:i-1}, P_{i:i-1})$$

- which implies

$$G_{i:j}, P_{i:j} = (G_{i:n}, P_{i:n}) \bullet (G_{m:j}, P_{m:j}) \text{ where } i \geq j \text{ and } m \geq n$$

32-bit carry skip adder

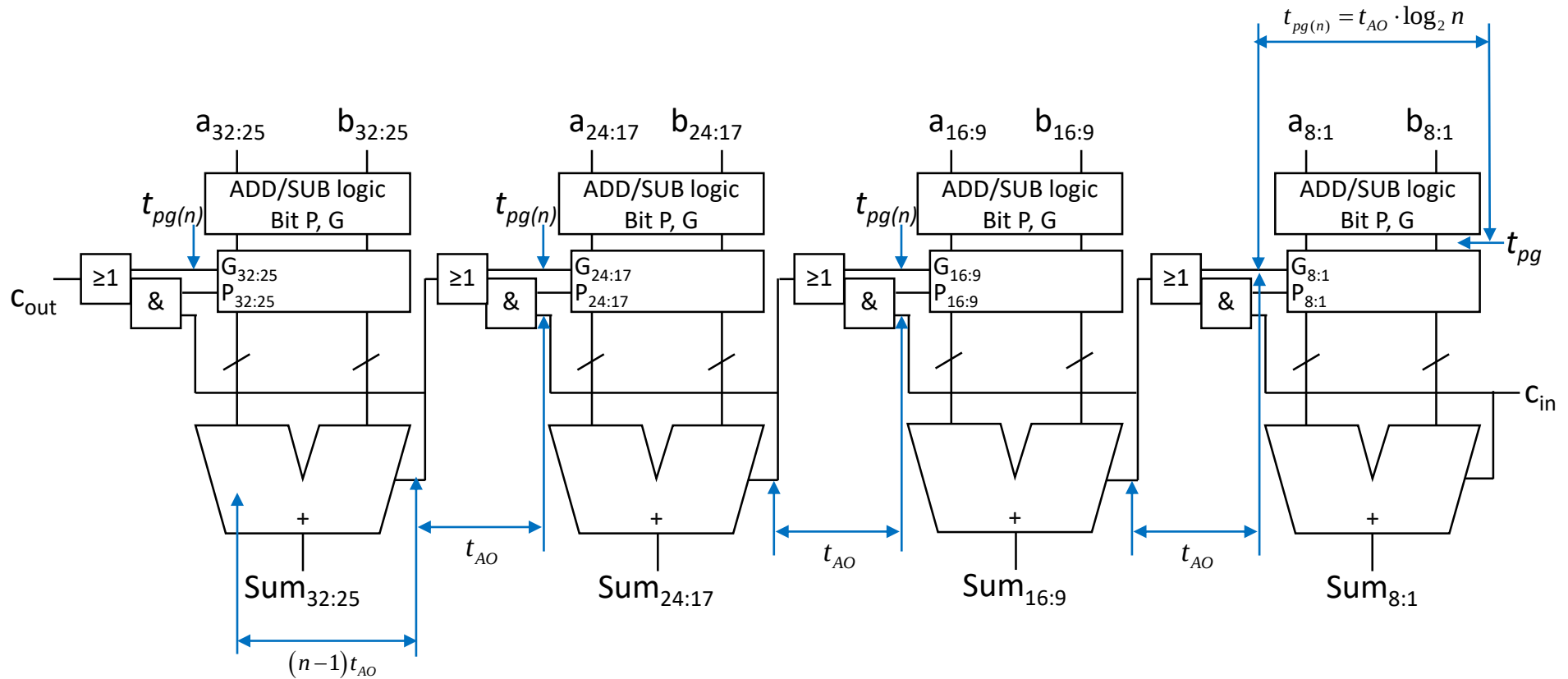
- Identify worst-case propagation delay for 32-bit adder!
- For N-bit adder built with k n -bit blocks!



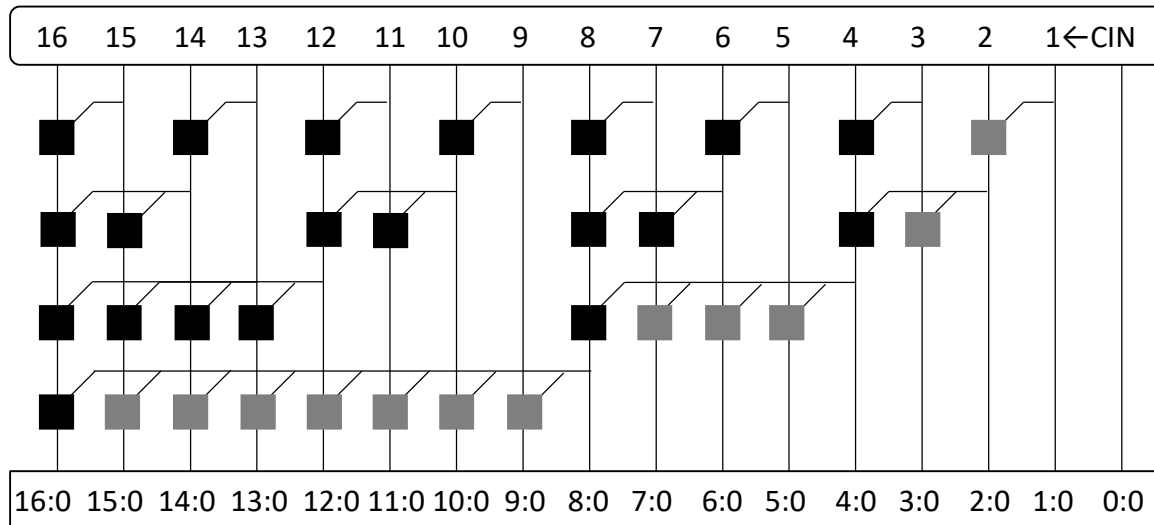
Determine the worst case delay!

$$t_{skip} = t_{pg} + 2(n-1)t_{AO} + (k-1)t_{mux} + t_{XOR}$$

32-bit carry-lookahead adder



Sklansky adder



Logic levels $L=4$
 Extra levels $l=0$
 Fanout $2^f+1=9$
 $f=3$
 Wire tracks $2^t=1$
 $t=0$
 $l+f+t=L-1=3$
 (0, 3, 0)

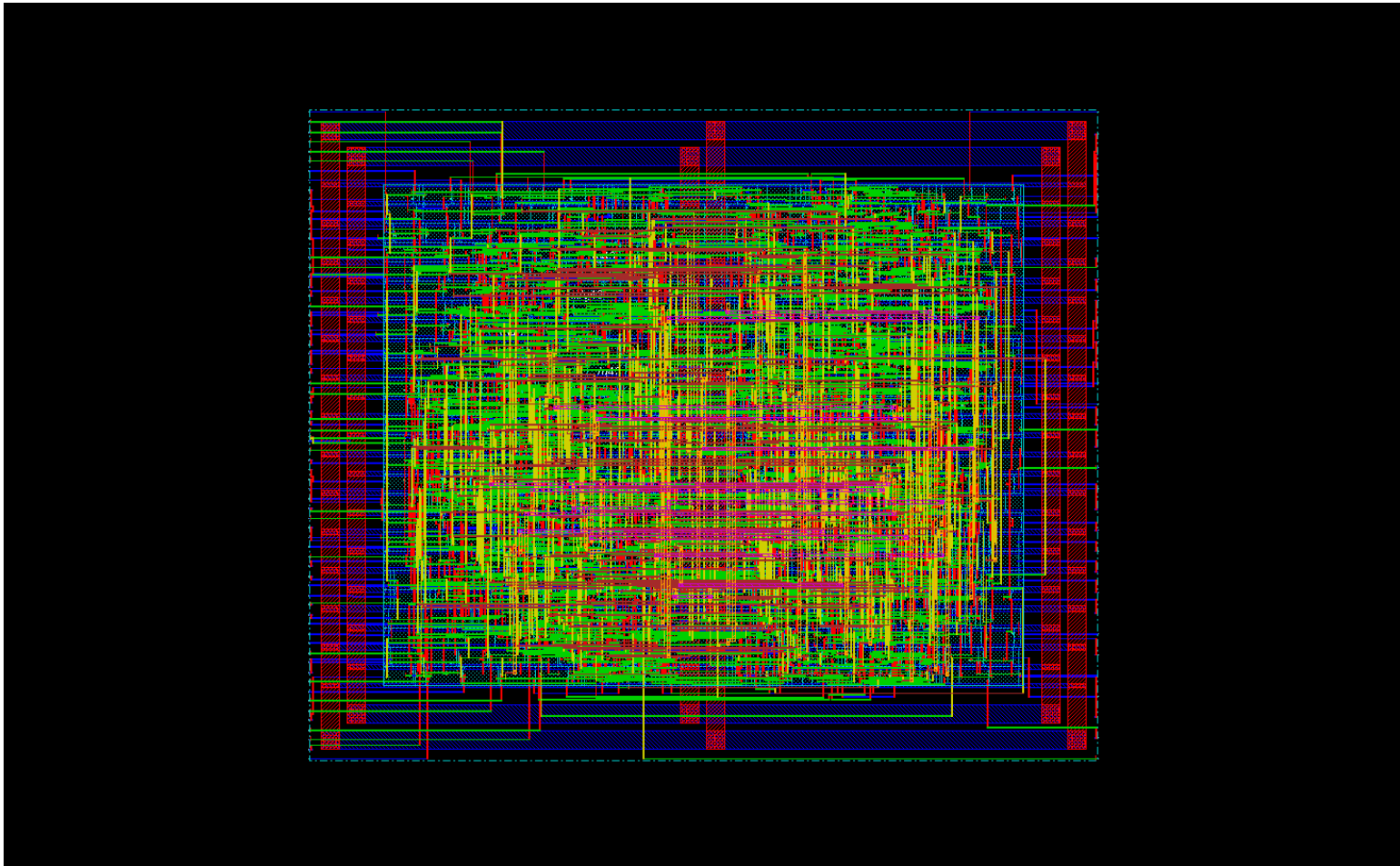
FIGURE 11.29 Tree adder PG networks

Determine the worst case delay!

$$t_{tree} = t_{pg} + t_{pg(n)} + t_{XOR}$$

$$t_{pg(n)} = \lceil \log_2 N \rceil t_{AO}$$

Example: synthesized 32-bit ALU layout



End of course wrap-up lecture!

Q & A?